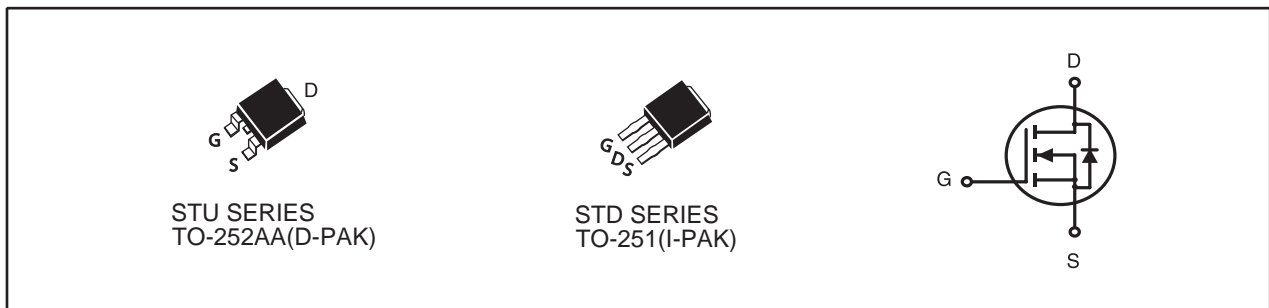


**N-Channel Logic Level Enhancement Mode Field Effect Transistor****PRODUCT SUMMARY**

V _{DSS}	I _D	R _{DS(ON)} (mΩ) Max
60V	50A	9.0 @ V _{GS} =10V
		13.2 @ V _{GS} =4.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- TO-252 and TO-251 Package.

**ABSOLUTE MAXIMUM RATINGS (T_C=25°C unless otherwise noted)**

Symbol	Parameter	Limit	Units
V _{DS}	Drain-Source Voltage	60	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous ^{a e}	T _C =25°C	50
		T _C =70°C	40
I _{DM}	-Pulsed ^b	146	A
E _{AS}	Single Pulse Avalanche Energy ^d	289	mJ
P _D	Maximum Power Dissipation	T _C =25°C	42
		T _C =70°C	27
T _J , T _{STG}	Operating Junction and Storage Temperature Range	-55 to 150	°C

THERMAL CHARACTERISTICS

R _{θJC}	Thermal Resistance, Junction-to-Case	3	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	50	°C/W

STU668S

STD668S

Ver 1.0

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	60			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48V, V _{GS} =0V			1	uA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±20V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	1.6	3	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =25A		6.5	9.0	m ohm
		V _{GS} =4.5V, I _D =20A		9.8	13.2	m ohm
g _{FS}	Forward Transconductance	V _{DS} =10V, I _D =25A		45		S
DYNAMIC CHARACTERISTICS ^c						
C _{ISS}	Input Capacitance	V _{DS} =25V, V _{GS} =0V f=1.0MHz		4760		pF
C _{OSS}	Output Capacitance			243		pF
C _{RSS}	Reverse Transfer Capacitance			209		pF
SWITCHING CHARACTERISTICS ^c						
t _{D(ON)}	Turn-On Delay Time	V _{DD} =30V I _D =1A V _{GS} =10V R _{GEN} = 6 ohm		60		ns
t _r	Rise Time			52		ns
t _{D(OFF)}	Turn-Off Delay Time			181		ns
t _f	Fall Time			47		ns
Q _g	Total Gate Charge	V _{DS} =30V, I _D =25A, V _{GS} =10V		55		nC
		V _{DS} =30V, I _D =25A, V _{GS} =4.5V		25		nC
Q _{gs}	Gate-Source Charge	V _{DS} =30V, I _D =25A, V _{GS} =10V		5		nC
Q _{gd}	Gate-Drain Charge			15		nC
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _S =7A		0.79	1.3	V

Notes

- Surface Mounted on FR4 Board, t ≤ 10sec.
- Pulse Test: Pulse Width ≤ 300us, Duty Cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.
- Starting T_J=25°C, L=0.5mH, V_{DD} = 30V. (See Figure13)
- Drain current limited by maximum junction temperature.

Sep,16,2013

STU668S STD668S

Ver 1.0

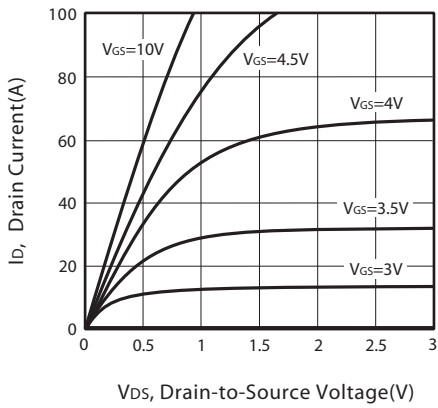


Figure 1. Output Characteristics

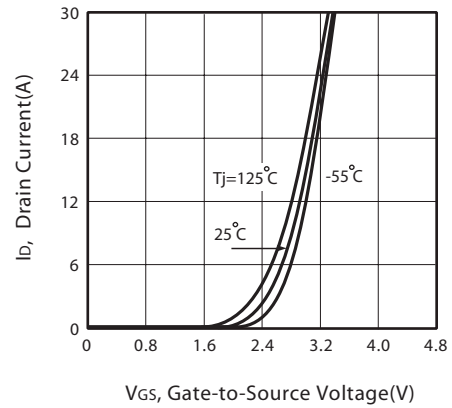


Figure 2. Transfer Characteristics

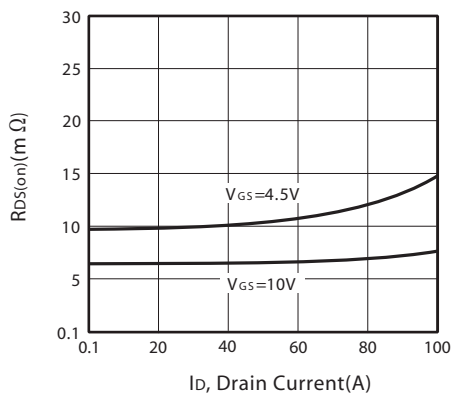


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

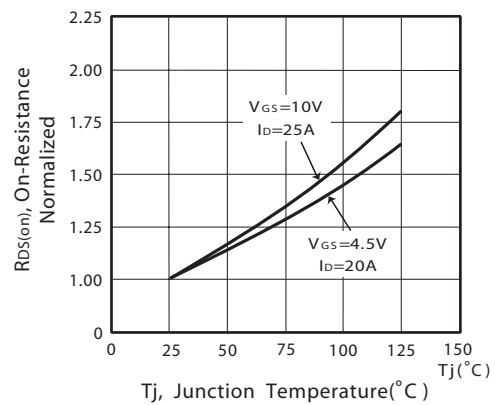


Figure 4. On-Resistance Variation with Drain Current and Temperature

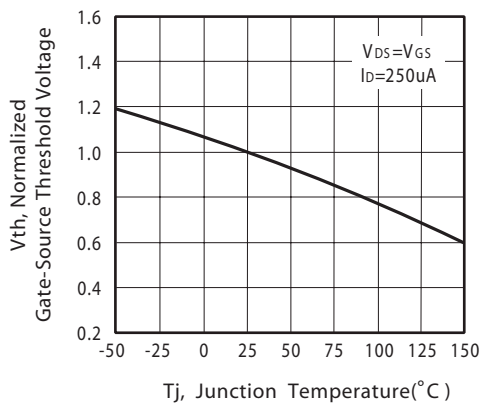


Figure 5. Gate Threshold Variation with Temperature

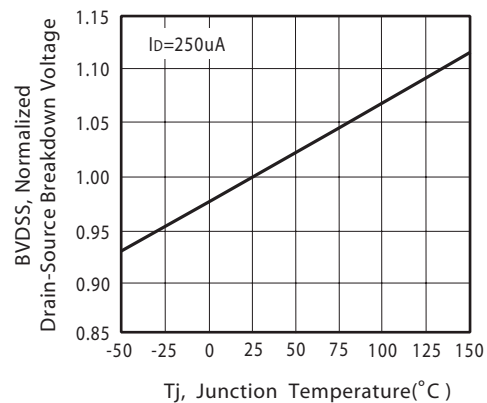


Figure 6. Breakdown Voltage Variation with Temperature

Sep,16,2013

STU668S STD668S

Ver 1.0

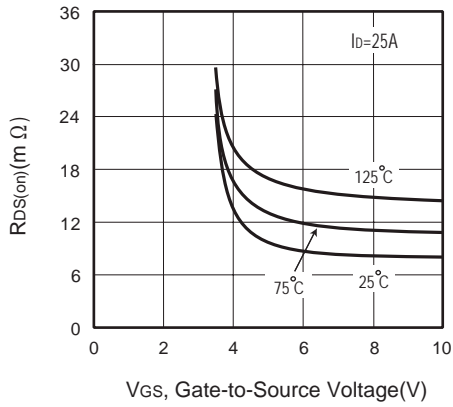


Figure 7. On-Resistance vs. Gate-Source Voltage

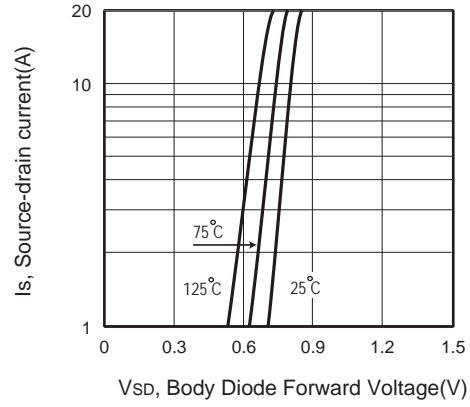


Figure 8. Body Diode Forward Voltage Variation with Source Current

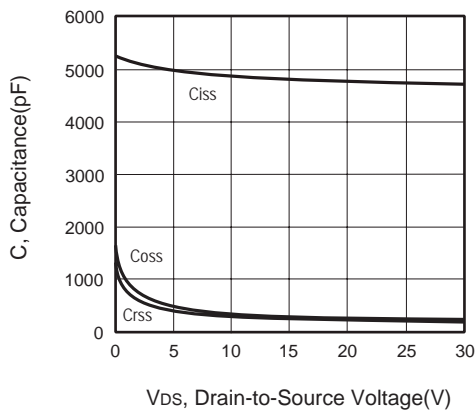


Figure 9. Capacitance

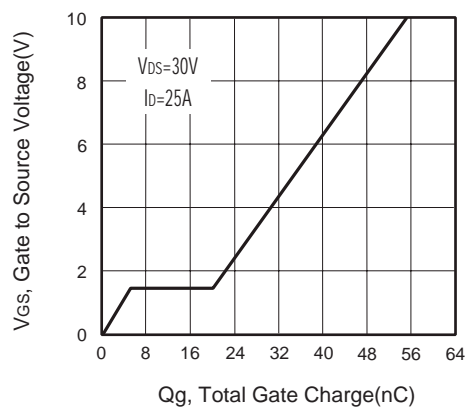


Figure 10. Gate Charge

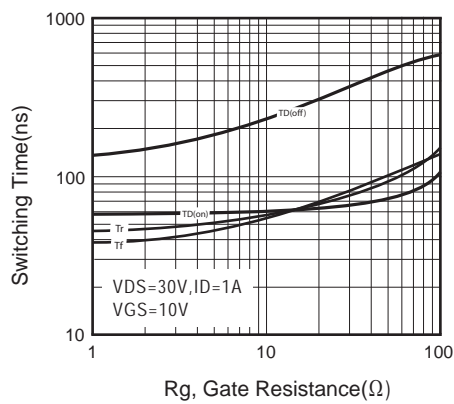


Figure 11. switching characteristics

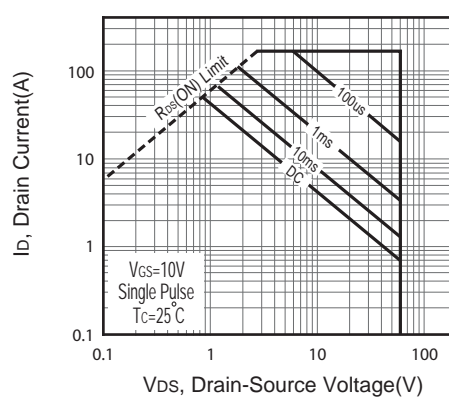
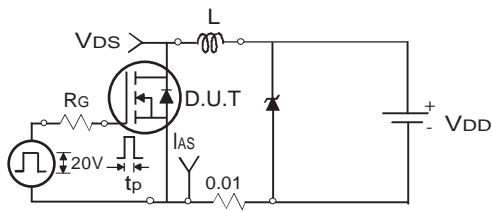


Figure 12. Maximum Safe Operating Area

Sep, 16, 2013

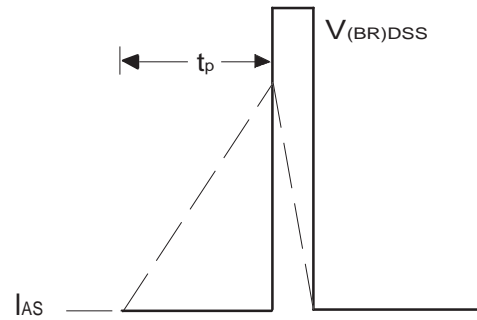
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Ver 1.0



Uncamped Inductive Test Circuit

Figure 13a.



Unclamped Inductive Waveforms

Figure 13b.

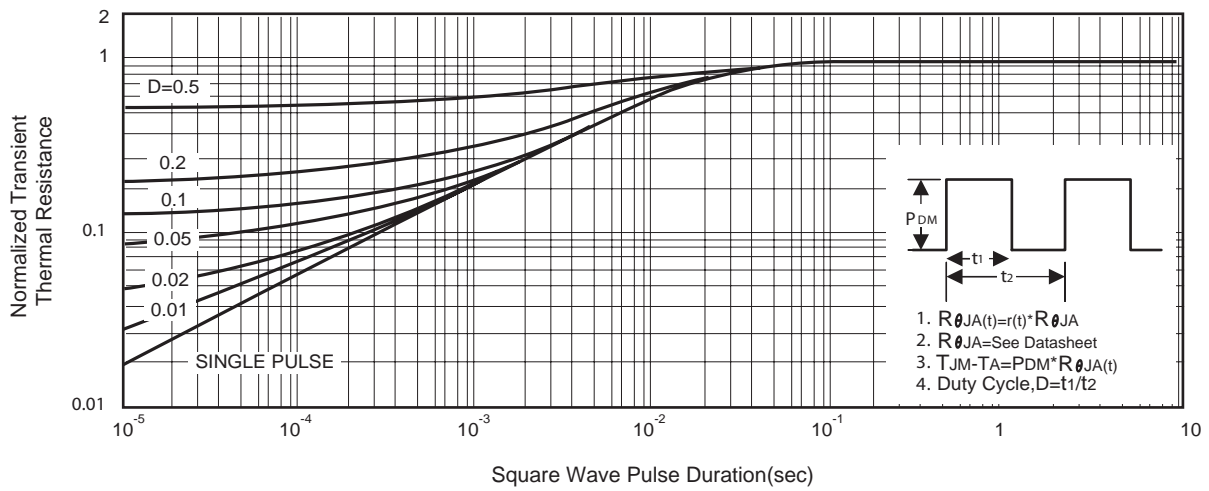


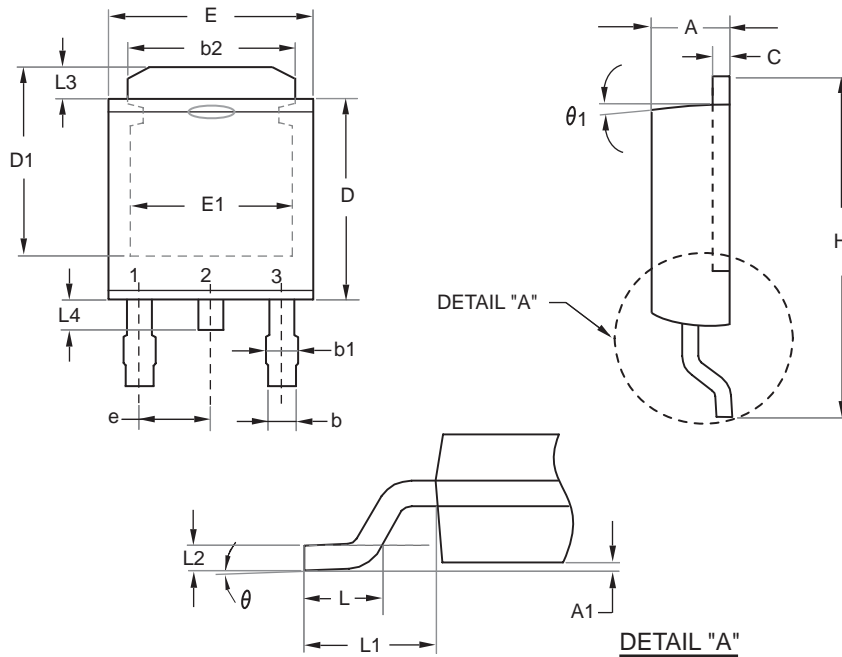
Figure 14. Normalized Thermal Transient Impedance Curve

Sep,16,2013

STU668S STD668S

Ver 1.0

TO-252



SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.000	0.200	0.000	0.008
b	0.400	0.889	0.016	0.035
b1	0.770	1.140	0.030	0.045
b2	4.800	5.460	0.189	0.215
C	0.400	0.600	0.016	0.024
D	5.300	6.223	0.209	0.245
D1	4.900	5.515	0.193	0.217
E	6.300	6.731	0.248	0.265
E1	4.400	5.004	0.173	0.197
e	2.290 REF		0.090 BSC	
H	8.900	10.400	0.350	0.409
L	1.397	1.770	0.055	0.070
L1	2.743 REF.		0.108 REF.	
L2	0.508 REF.		0.020 REF.	
L3	0.890	1.700	0.035	0.067
L4	0.500	1.100	0.020	0.043
theta	0°	10°	0°	10°
theta1	7° REF.		7° REF.	

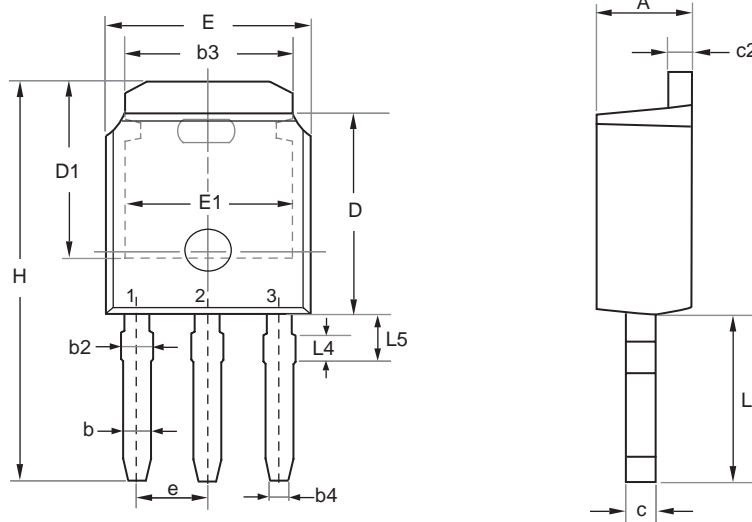
Sep,16,2013

STU668S STD668S

Ver 1.0

PACKAGE OUTLINE DIMENSIONS

TO-251



SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
E	6.400	6.731	0.252	0.265
L	3.980	4.280	0.157	0.169
L4	0.698 REF		0.027 REF	
L5	0.972	1.226	0.038	0.048
D	6.000	6.223	0.236	0.245
H	11.050	11.450	0.435	0.450
b	0.640	0.880	0.025	0.035
b2	0.770	1.140	0.030	0.045
b3	5.210	5.460	0.205	0.215
b4	0.450	0.550	0.018	0.022
e	2.286 BSC		0.090 BSC	
A	2.200	2.380	0.087	0.094
c	0.400	0.600	0.016	0.024
c2	0.400	0.600	0.016	0.024
D1	5.100	---	0.201	---
E1	4.400	---	0.173	---

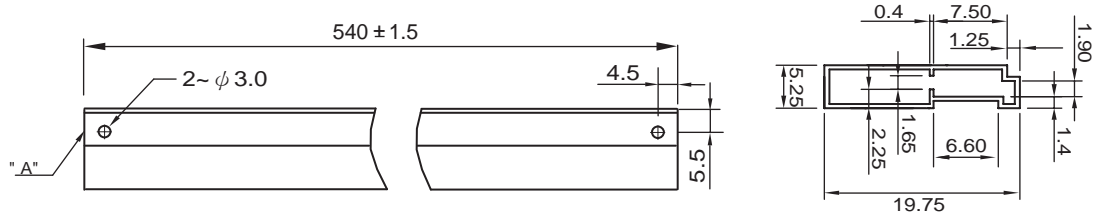
Sep,16,2013

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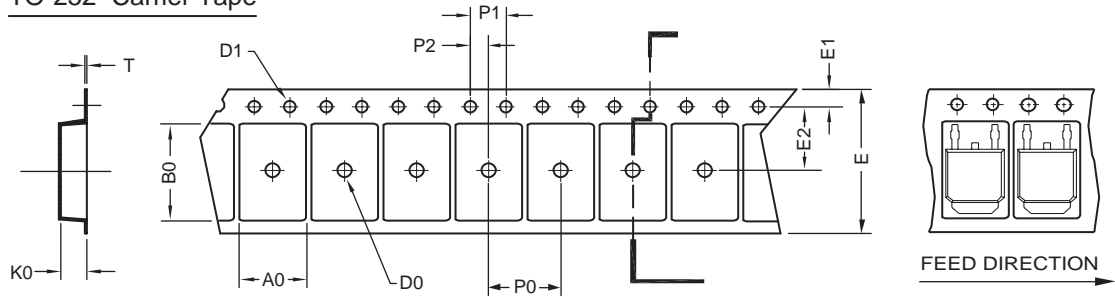
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TO-251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



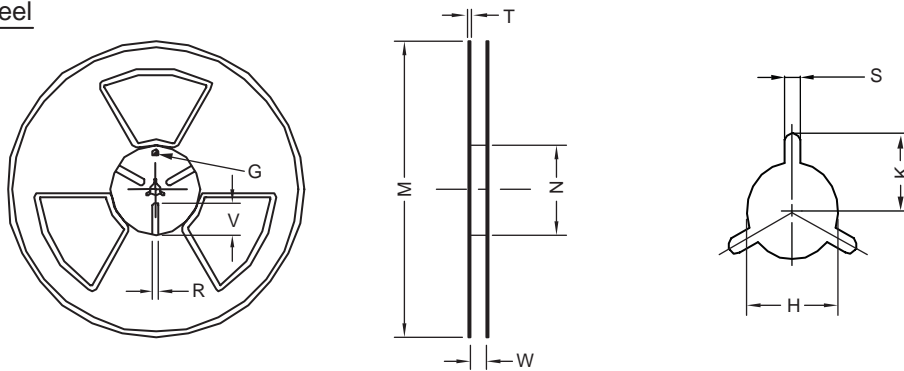
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
TO-252 (16 mm)	6.96 ±0.1	10.49 ±0.1	2.79 ±0.1	φ 2	φ 1.5 + 0.1 - 0	16.0 ±0.3	1.75 ±0.1	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



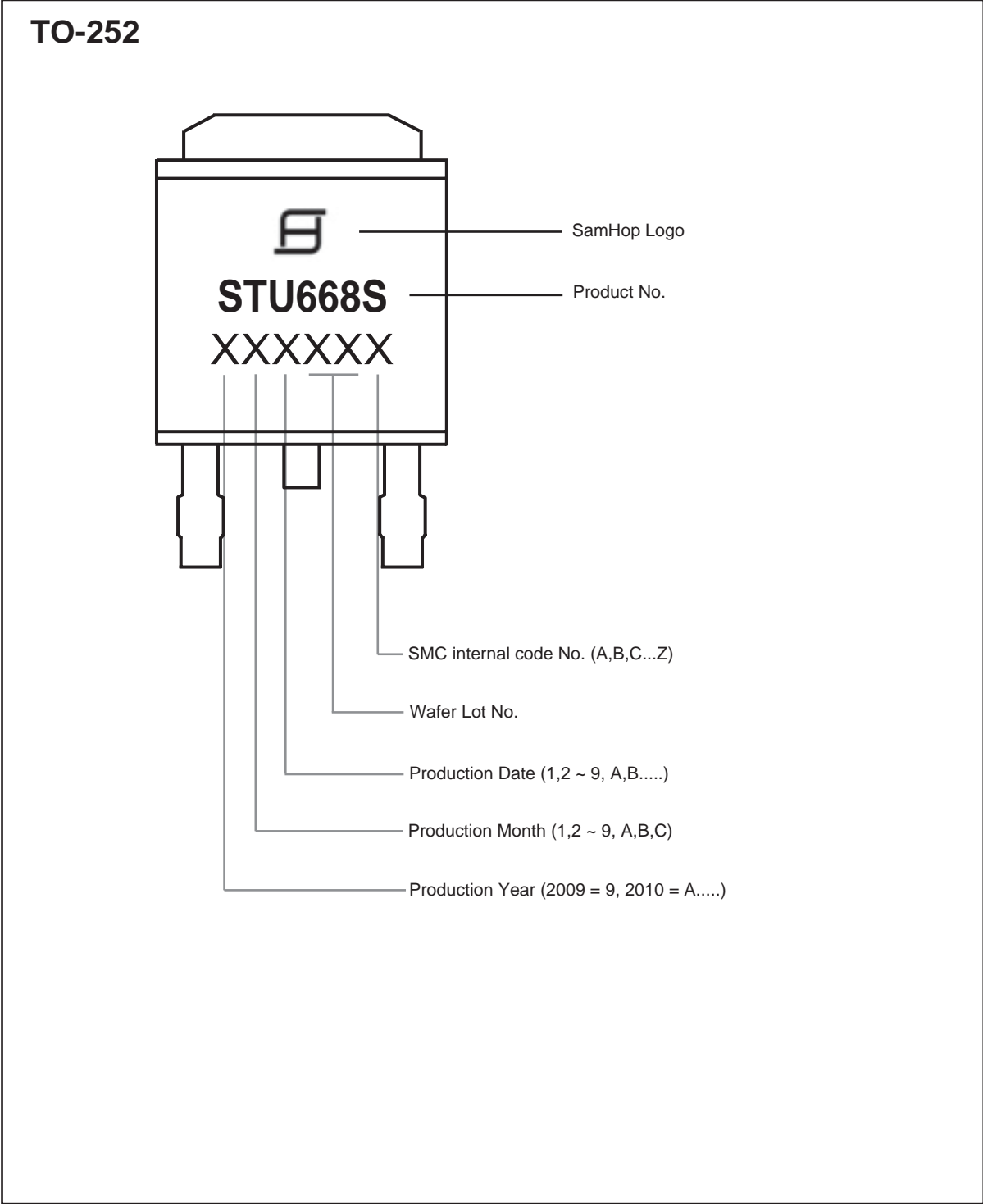
UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	φ 330	φ 330 ± 0.5	φ 97 ± 1.0	17.0 + 1.5 - 0	2.2	φ 13.0 + 0.5 - 0.2	10.6	2.0 ±0.5	---	---	---

Sep,16,2013

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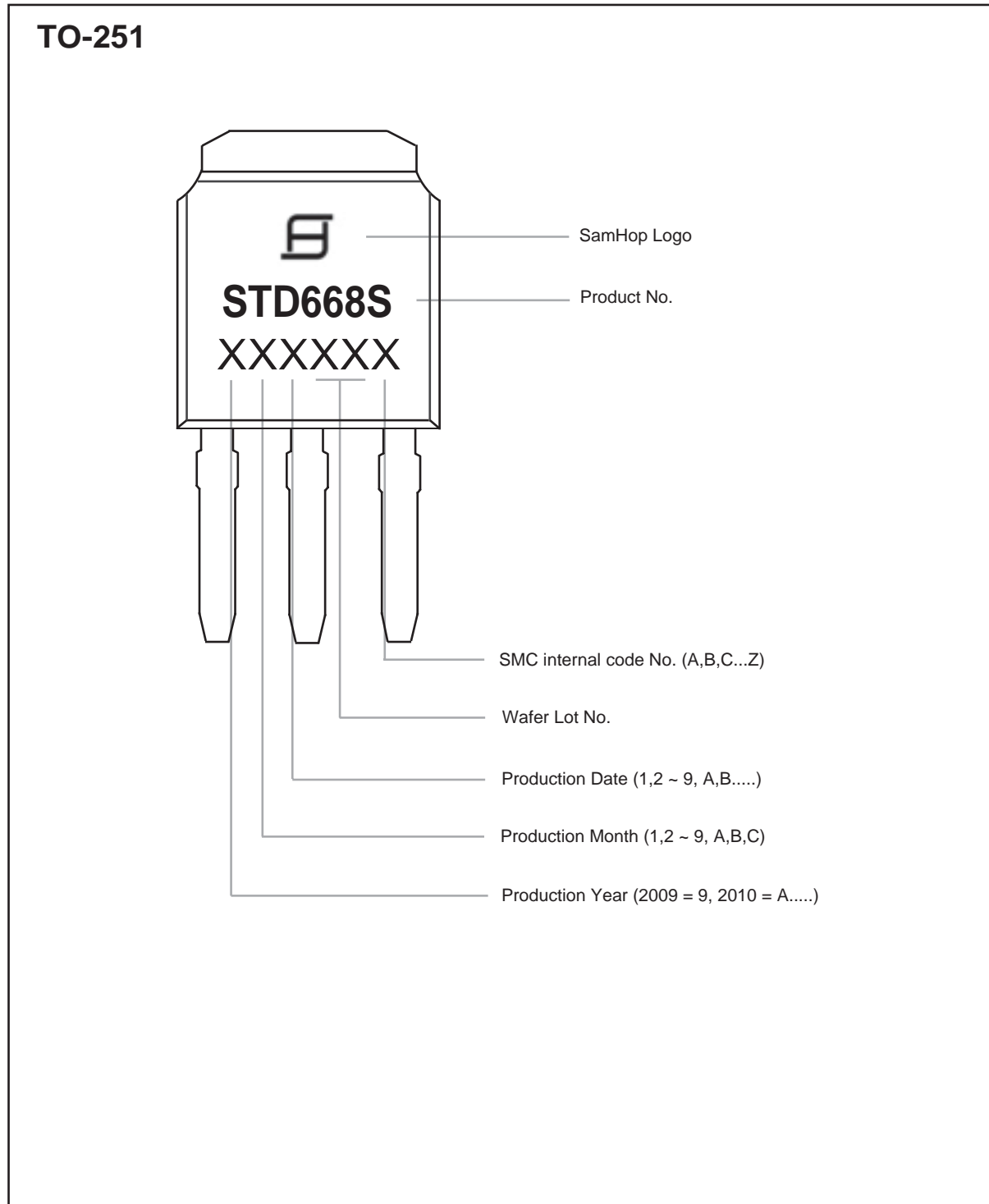
TOP MARKING DEFINITION



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Sep,16,2013